

Interconnect Width Selection for Deep Submicron Designs using the Table Lookup Method

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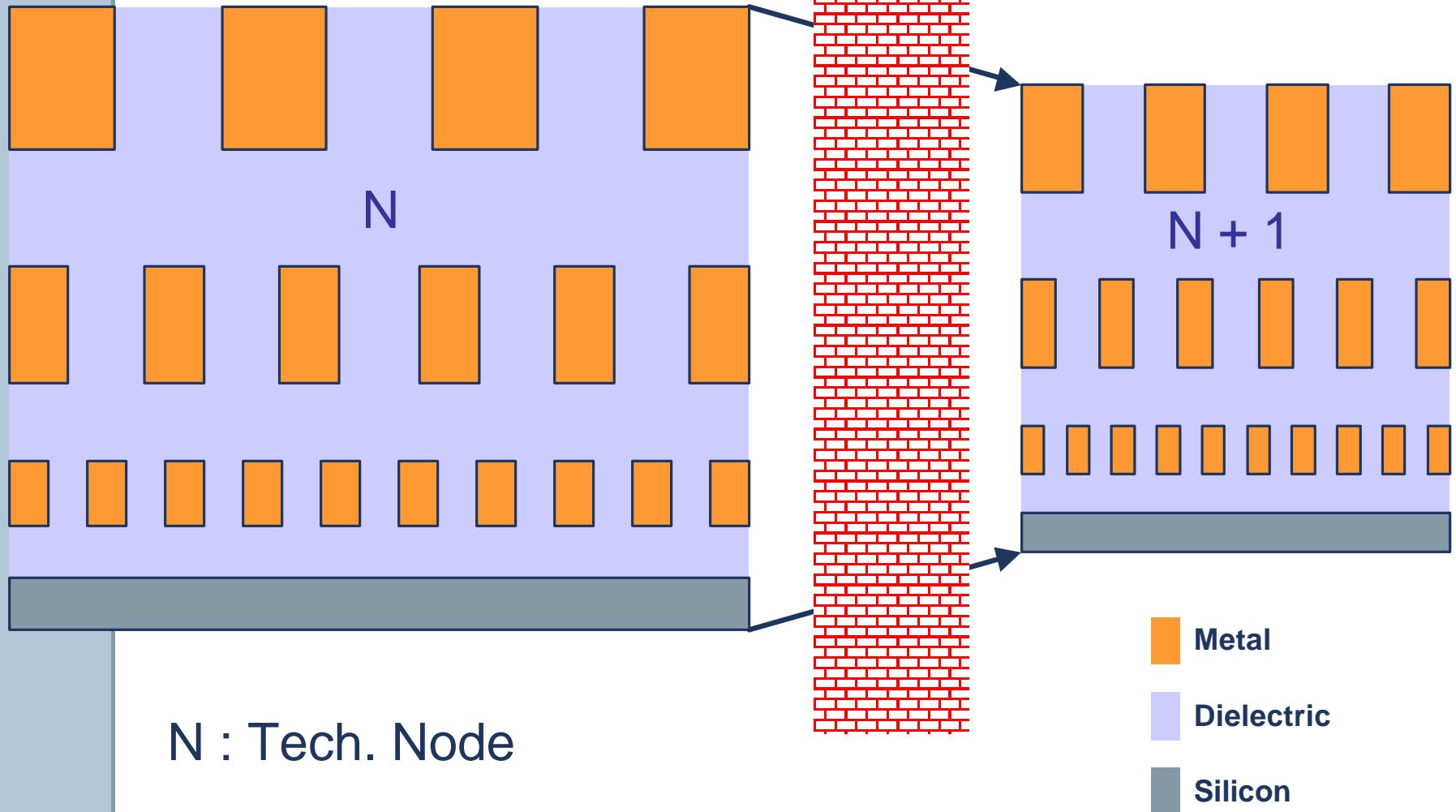
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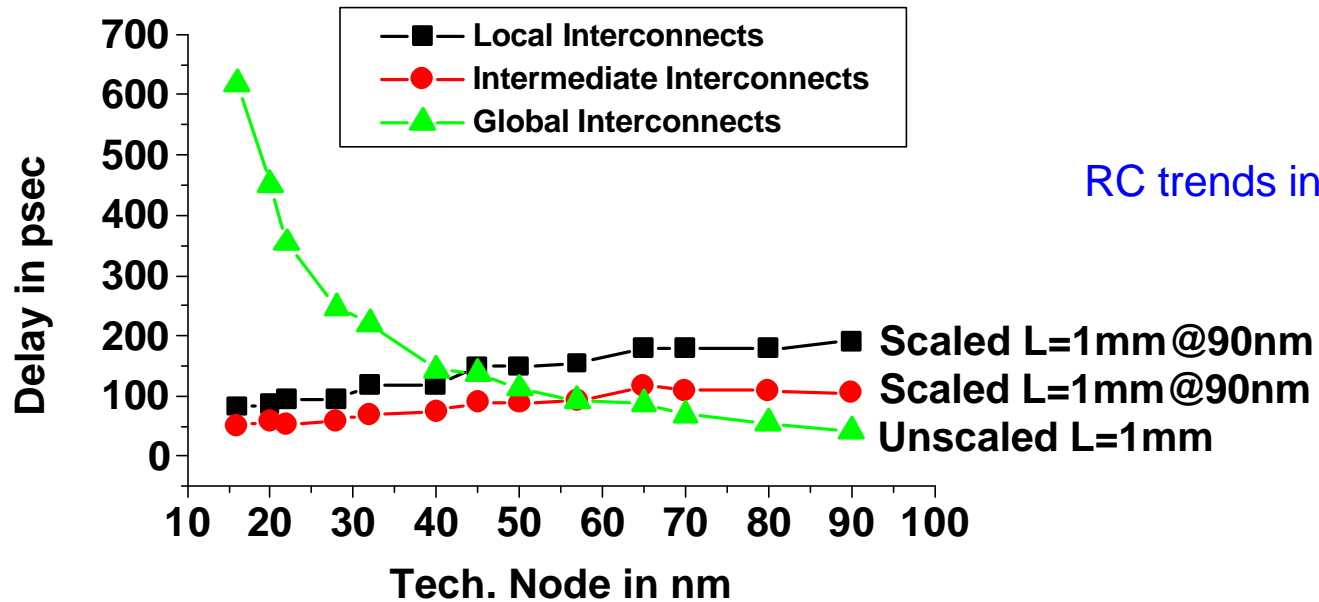
SLIP'2004, Paris

14-15 February ,2004

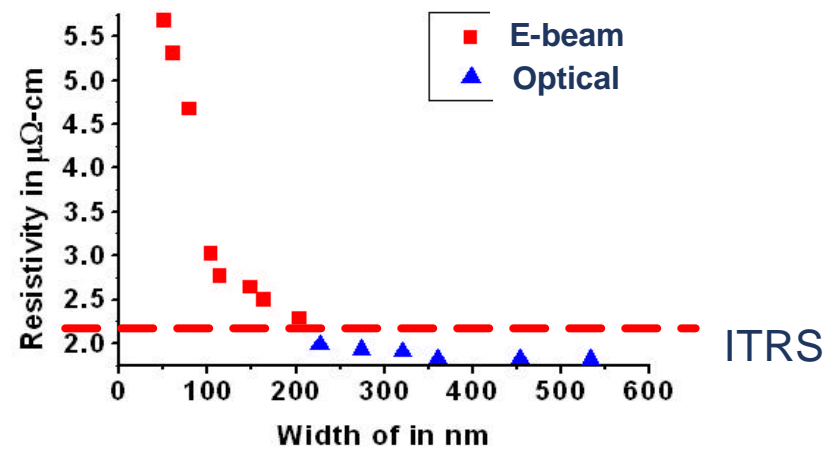
Backend Technology

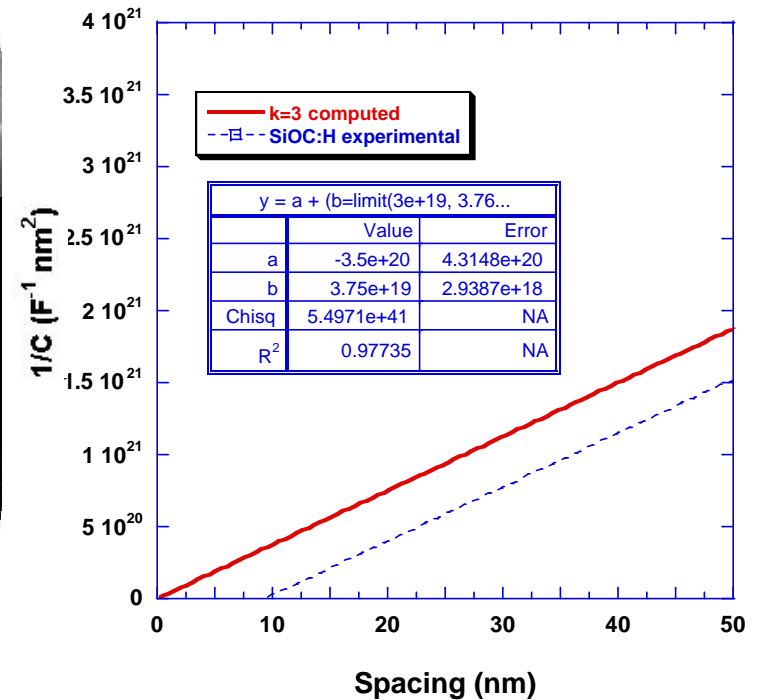
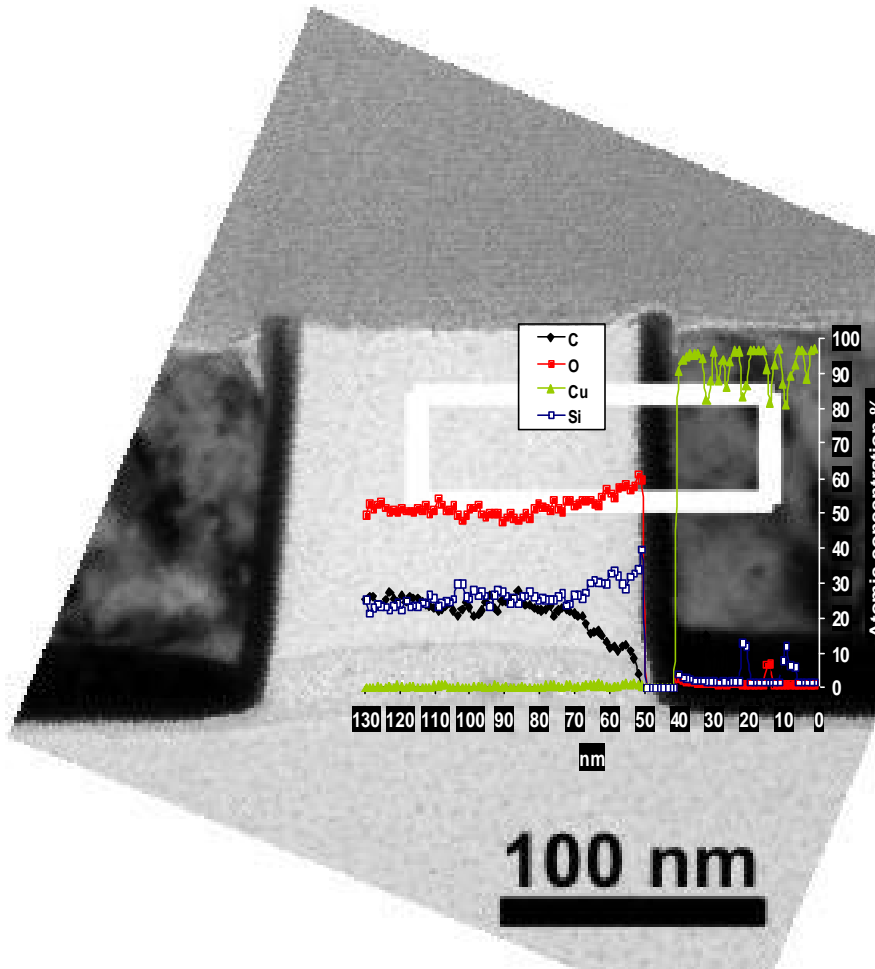


N : Tech. Node



W. Wu, R. Jonckheere, M. Stucchi, H. Struyf, Z. Tokei, I. Vervoort, I. Vos, F. Iacopi, and K. Maex, Studies on Resistivity of Narrow Cu Interconnects, Proceedings of Advanced Metallization Conference, pp. 345-348, (San Diego, October 2002)





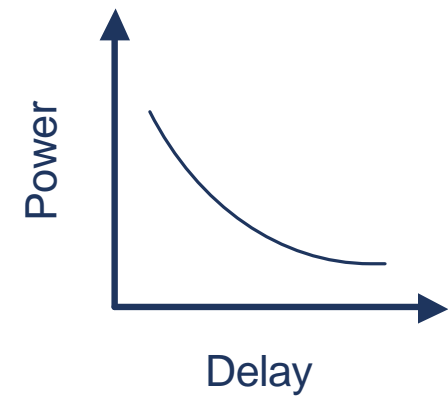
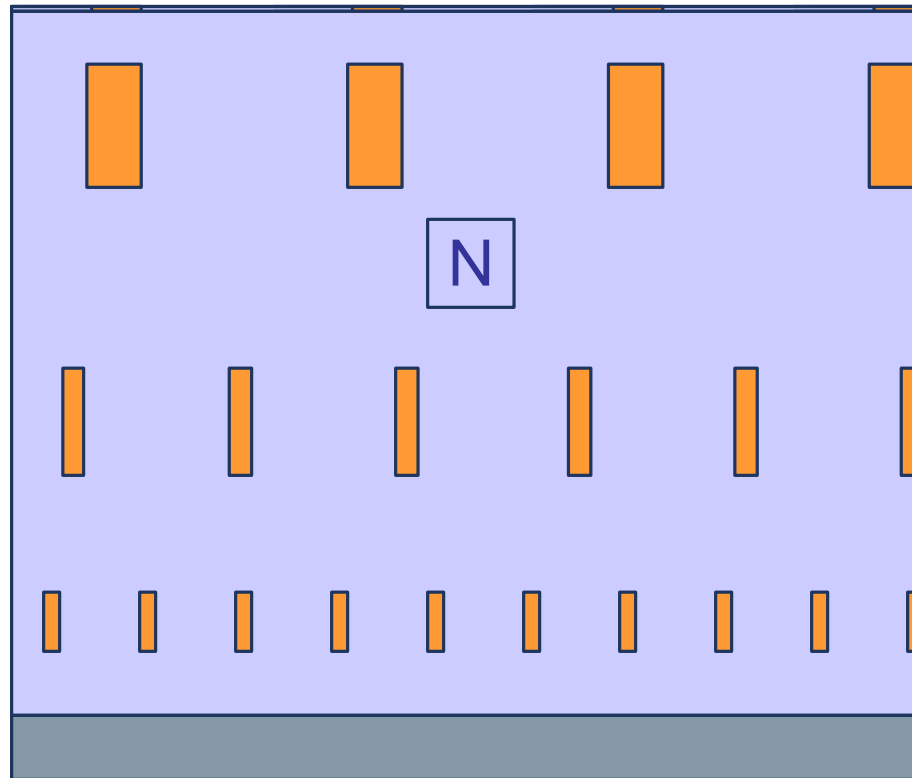
F. Iacopi, M. Stucchi, O. Richard and K. Maex,
 "Electrical Equivalent Sidewall Damage in
 Patterned Low-k Dielectrics", to appear in
 Electrochemical and Solid-State Letters, 2004.

**'Electrical equivalent
 sidewall damage'**

S' ~ 10nm!

Let us assume that scaling continues in spite of DSM issues

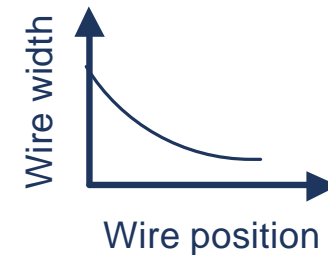
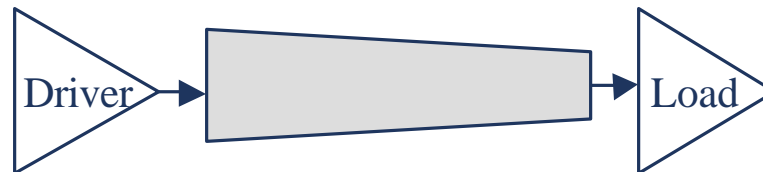
Width and Height exploration for constant pitch



-  Metal
-  Dielectric
-  Silicon

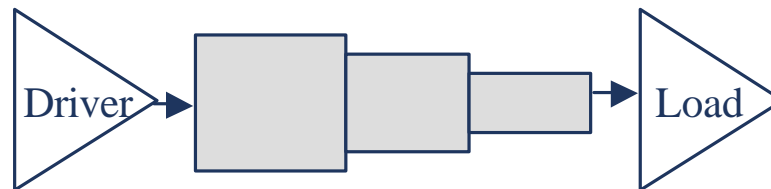
Interconnect Width Sizing

- Width Sizing [Lee2000,Alpert2001,Cong2002,Jiang2001]
 - Decreasing the wire width progressively from source to sink.(TWS)



- Multiple Width Sizing (MWS or TWS)

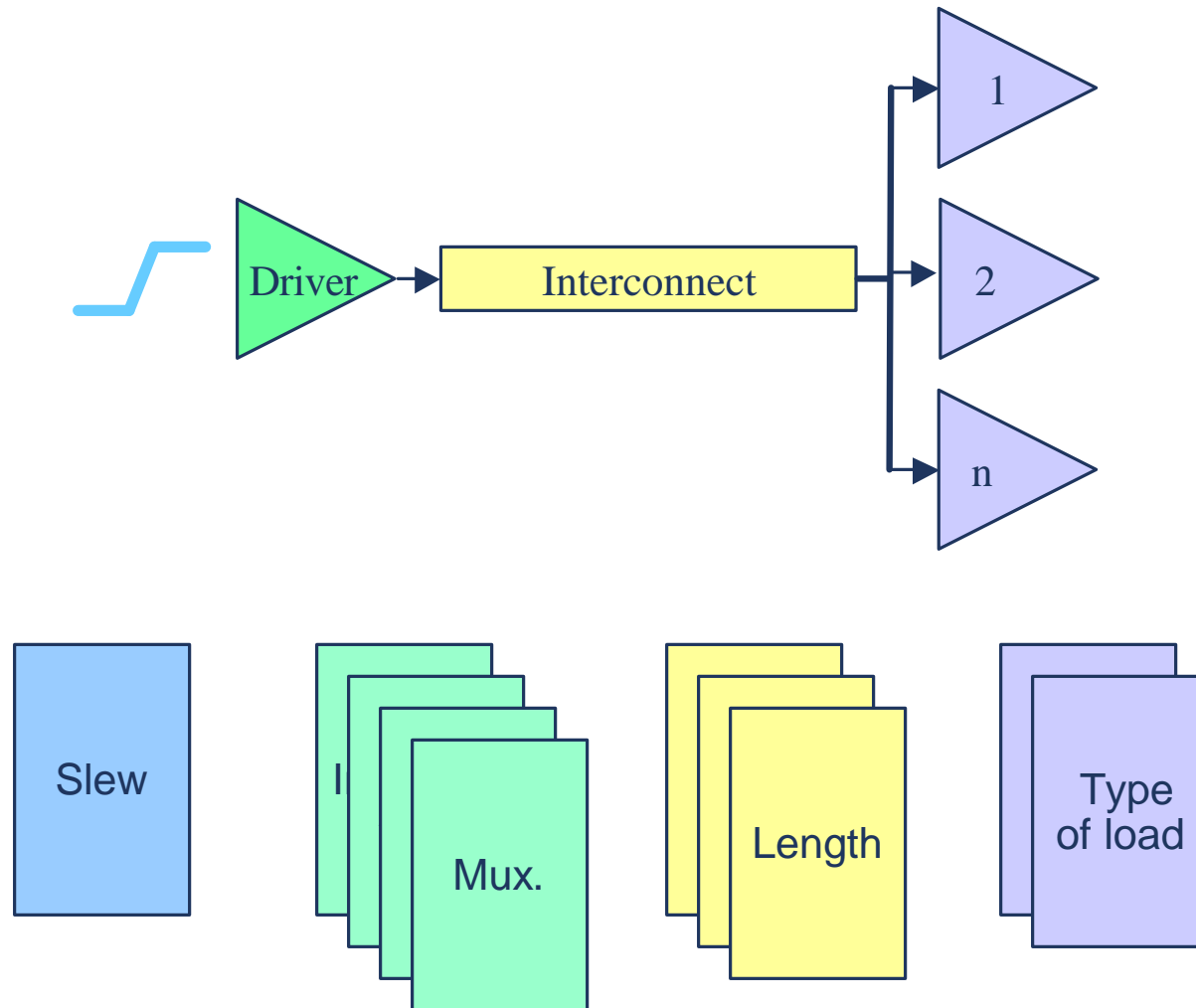
} Problems with routing



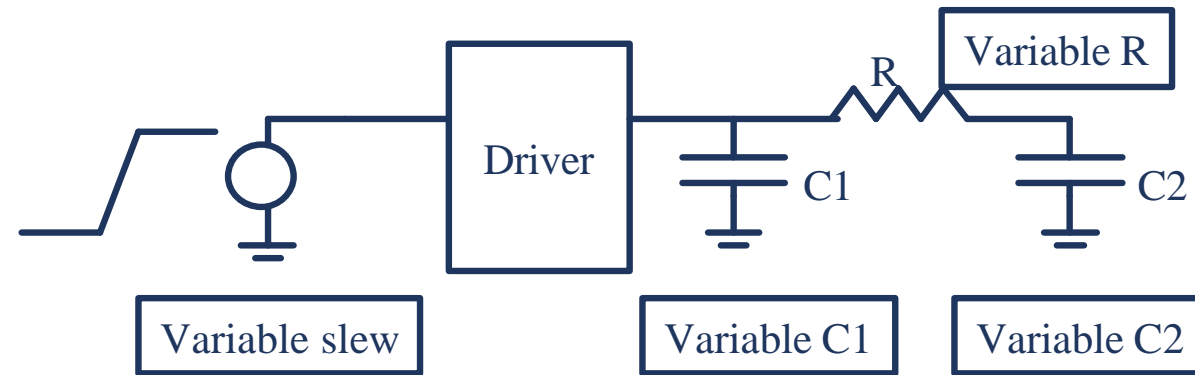
- Uniform Width Sizing (UWS)



Interconnect Width Selection by Table Lookup Method



4-D Lookup Table

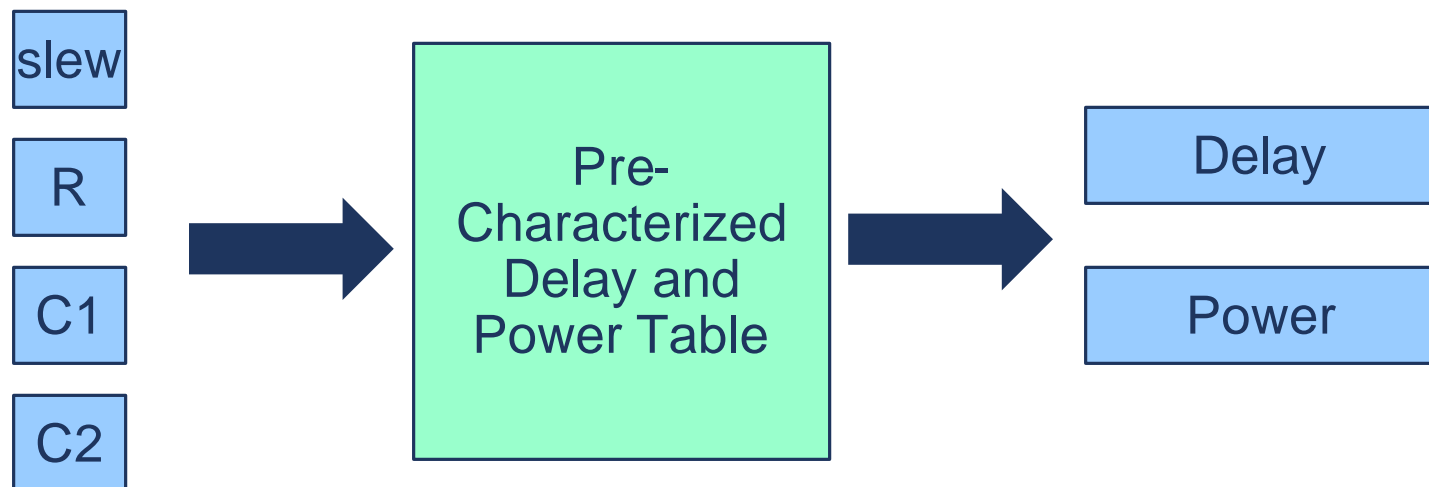


$$R = 0.48R_{int}$$

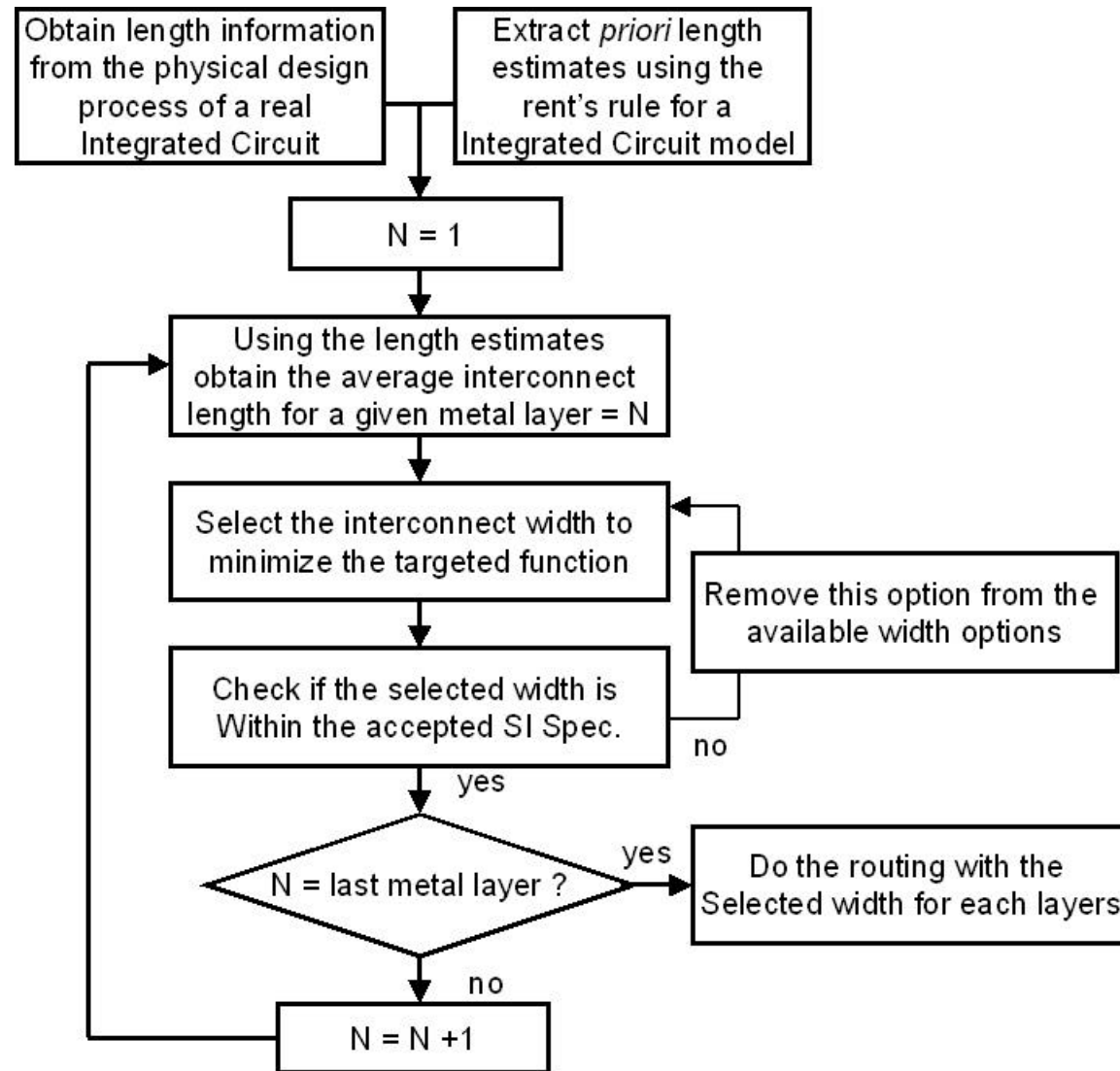
$$C1 = 1/6C_{int}$$

$$C2 = 5/6C_{int} + C_L$$

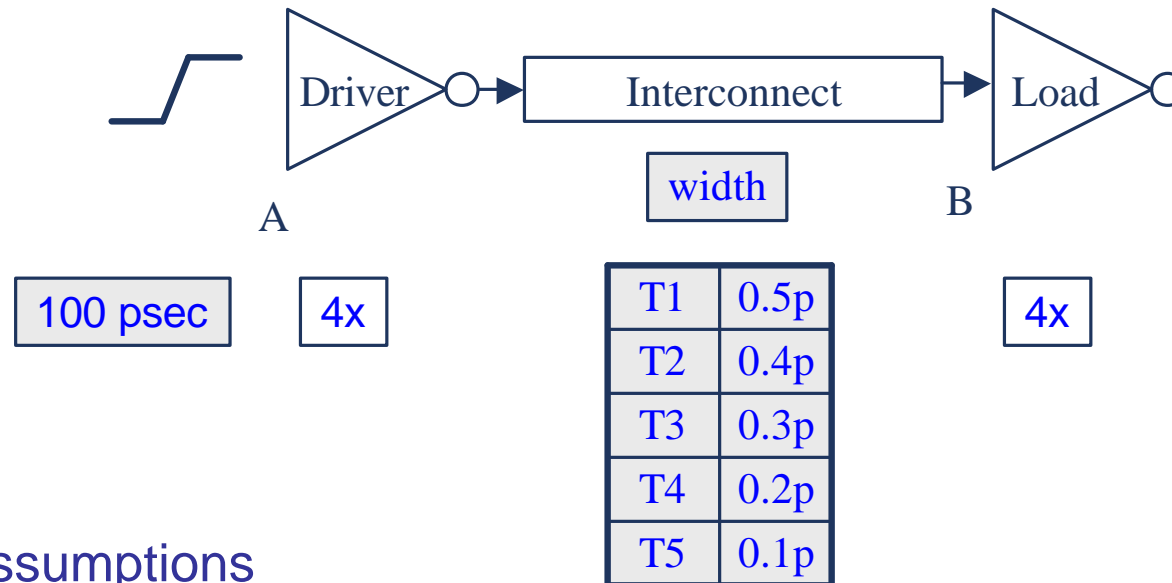
O'Brien/Savarino pi Model



Exploration Methodology (Case Study-1)



Circuit Example (2 pin net)

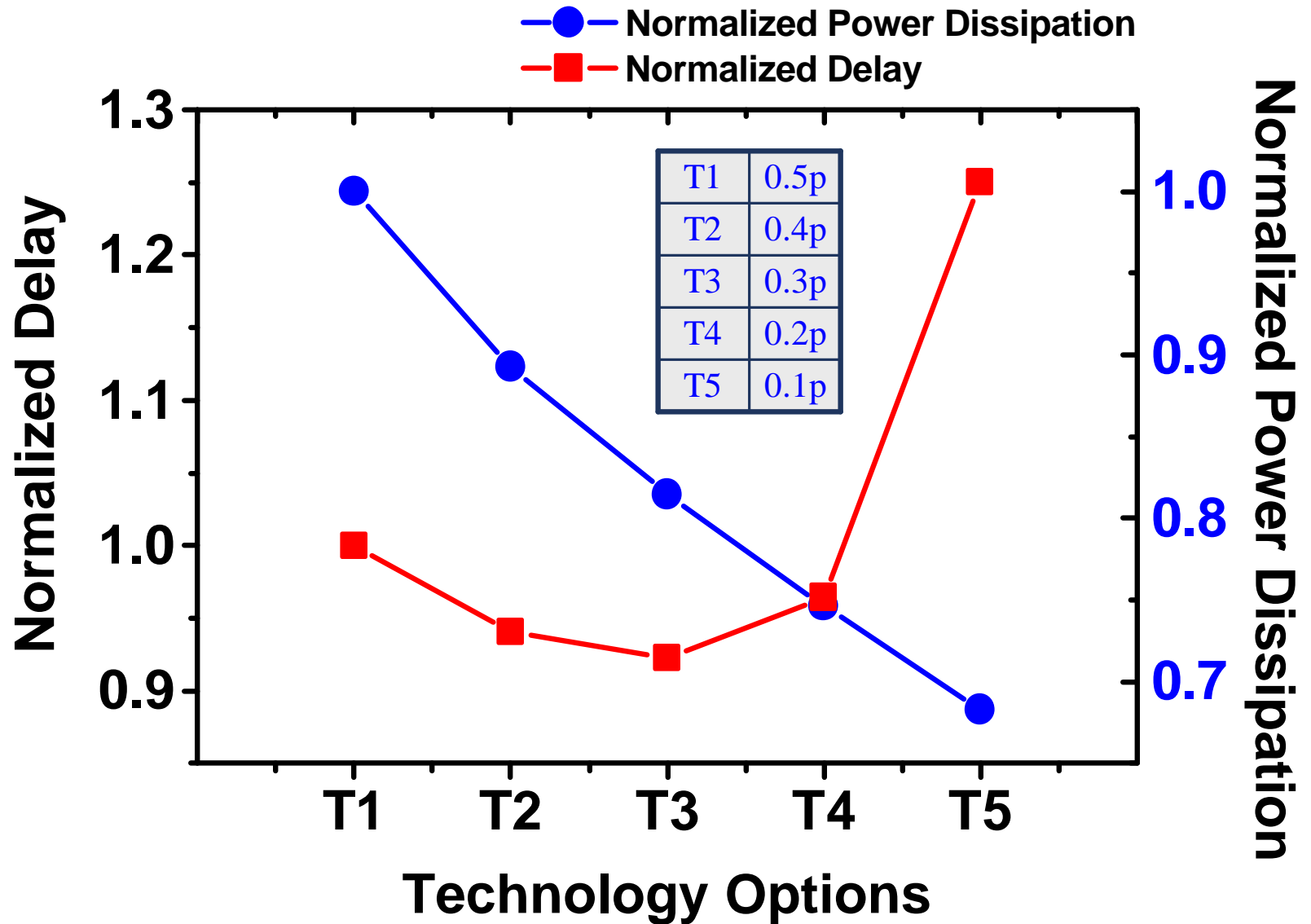


Assumptions

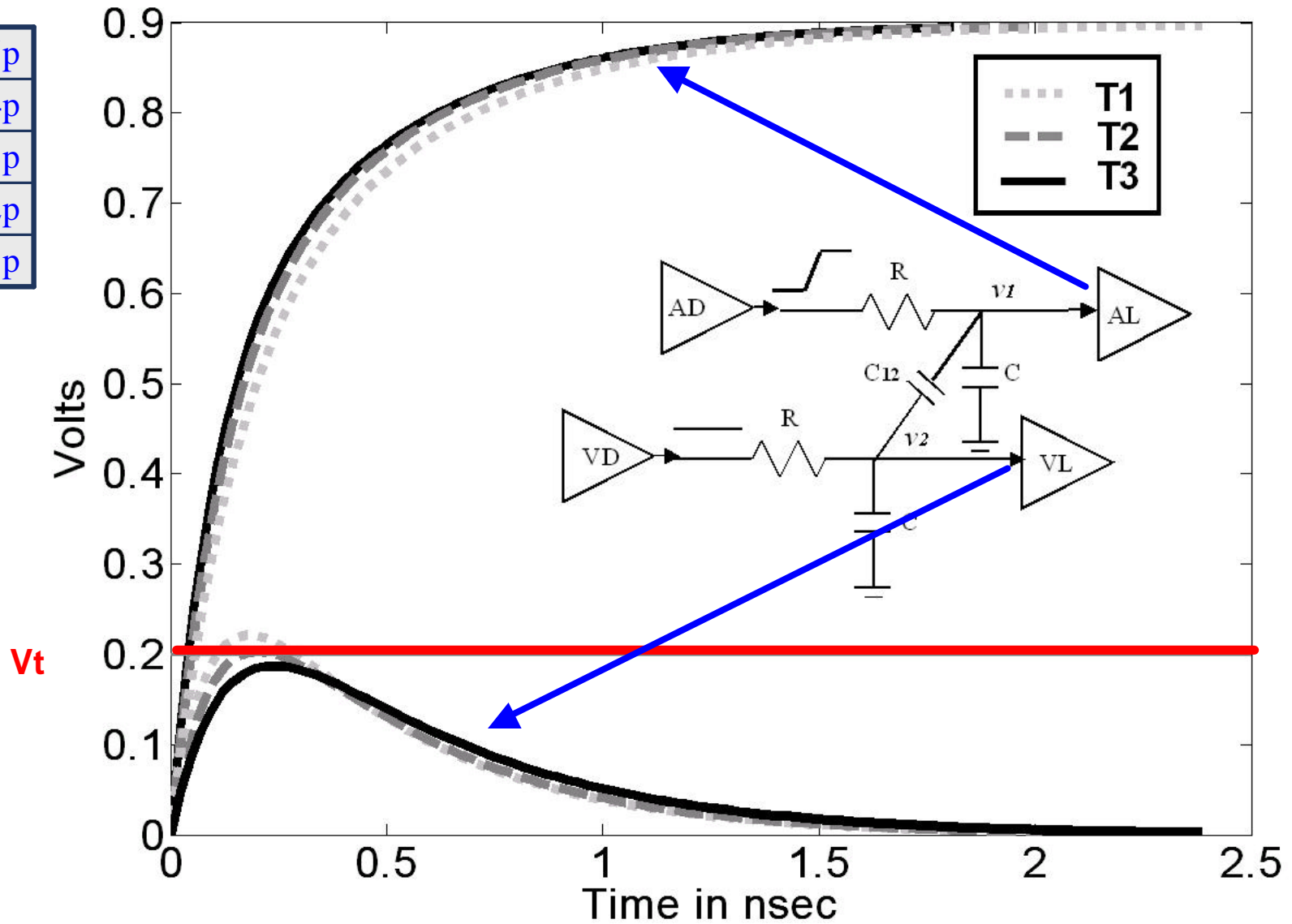
- Exploration for 45 nm node
- Length information obtained by using rent's rule for a simple isotropic model of an IC (a priori length information)
- Analysis done for average wire length in 2nd layer (440 um)
- Driver and load both are 4x inverters
 - 45nm BSIM4 model card used [1]
- One width per layer assumed
- $T_{A \rightarrow B}$ and Total power dissipation were calculated

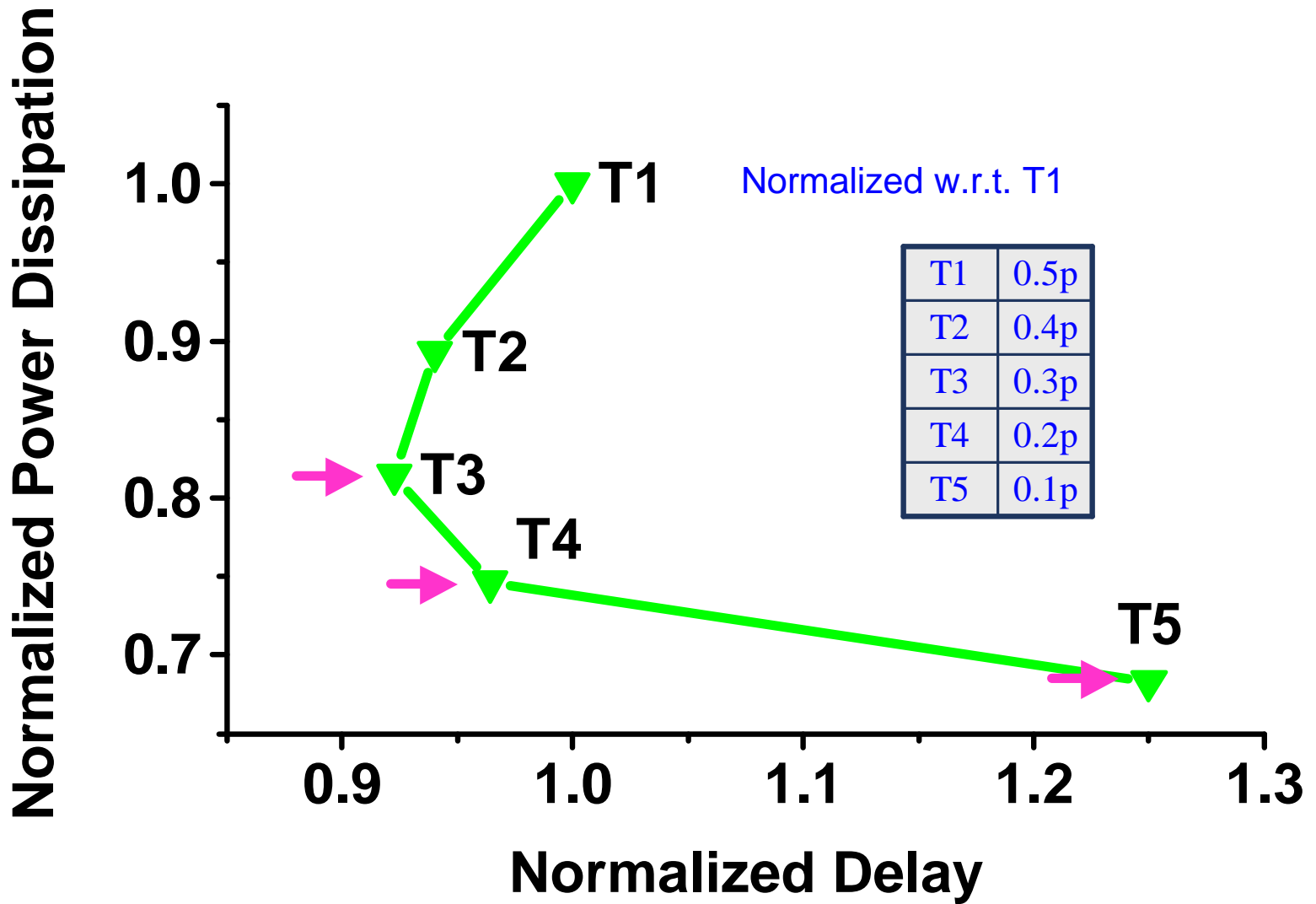
[1] <http://www-device.eecs.berkeley.edu/~ptm>

Exploration of width for optimizing delay

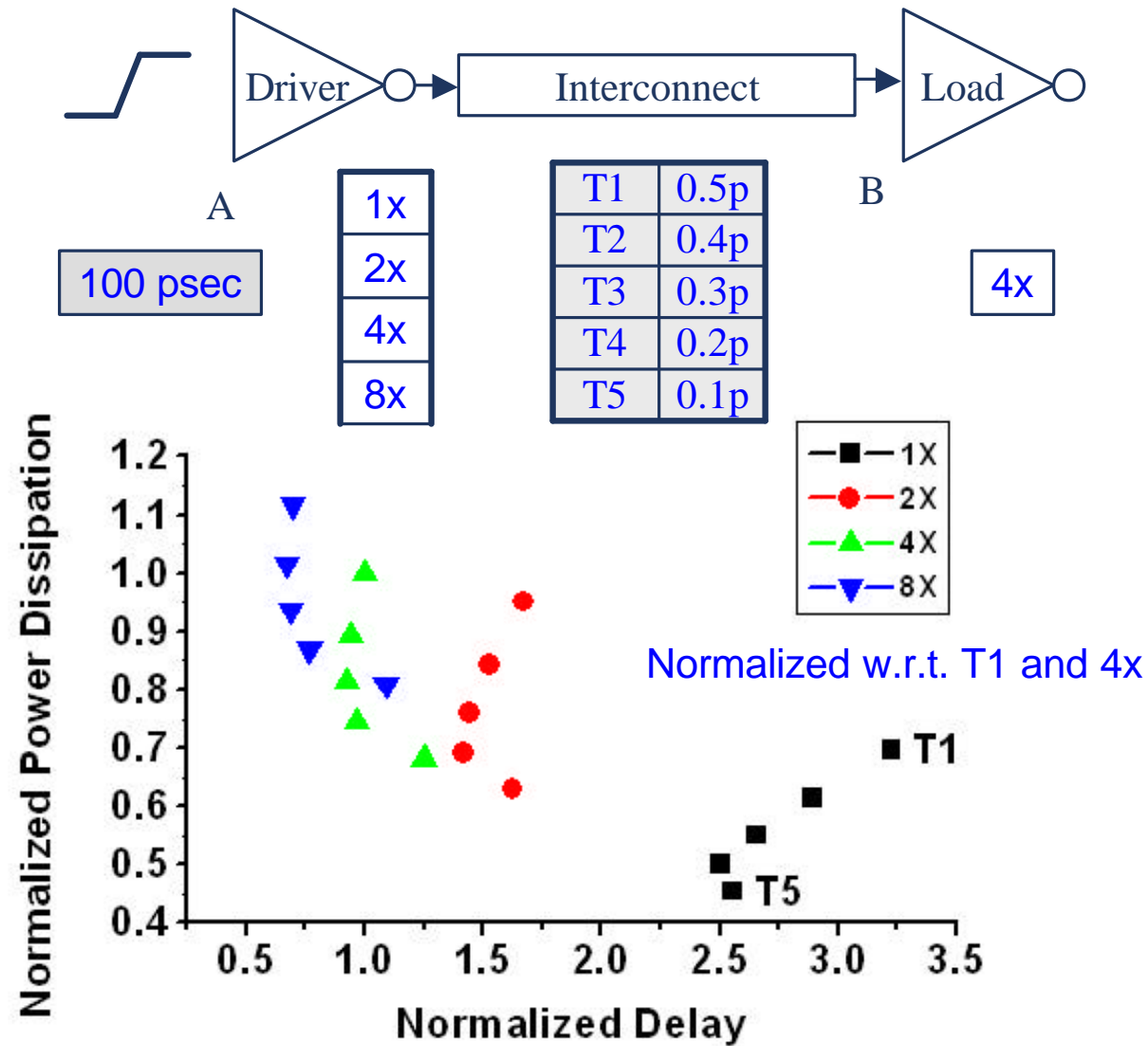


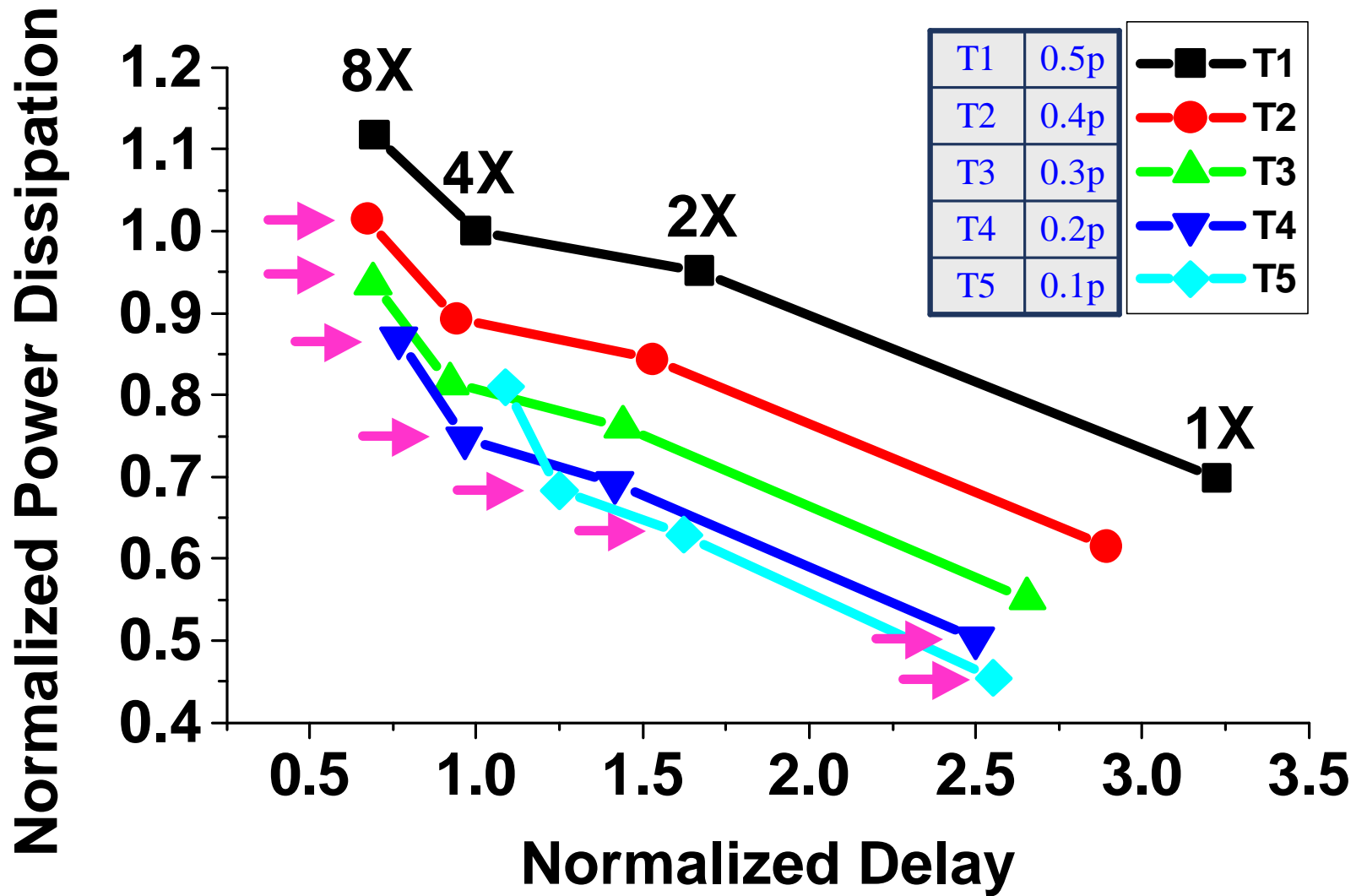
T1	0.5p
T2	0.4p
T3	0.3p
T4	0.2p
T5	0.1p



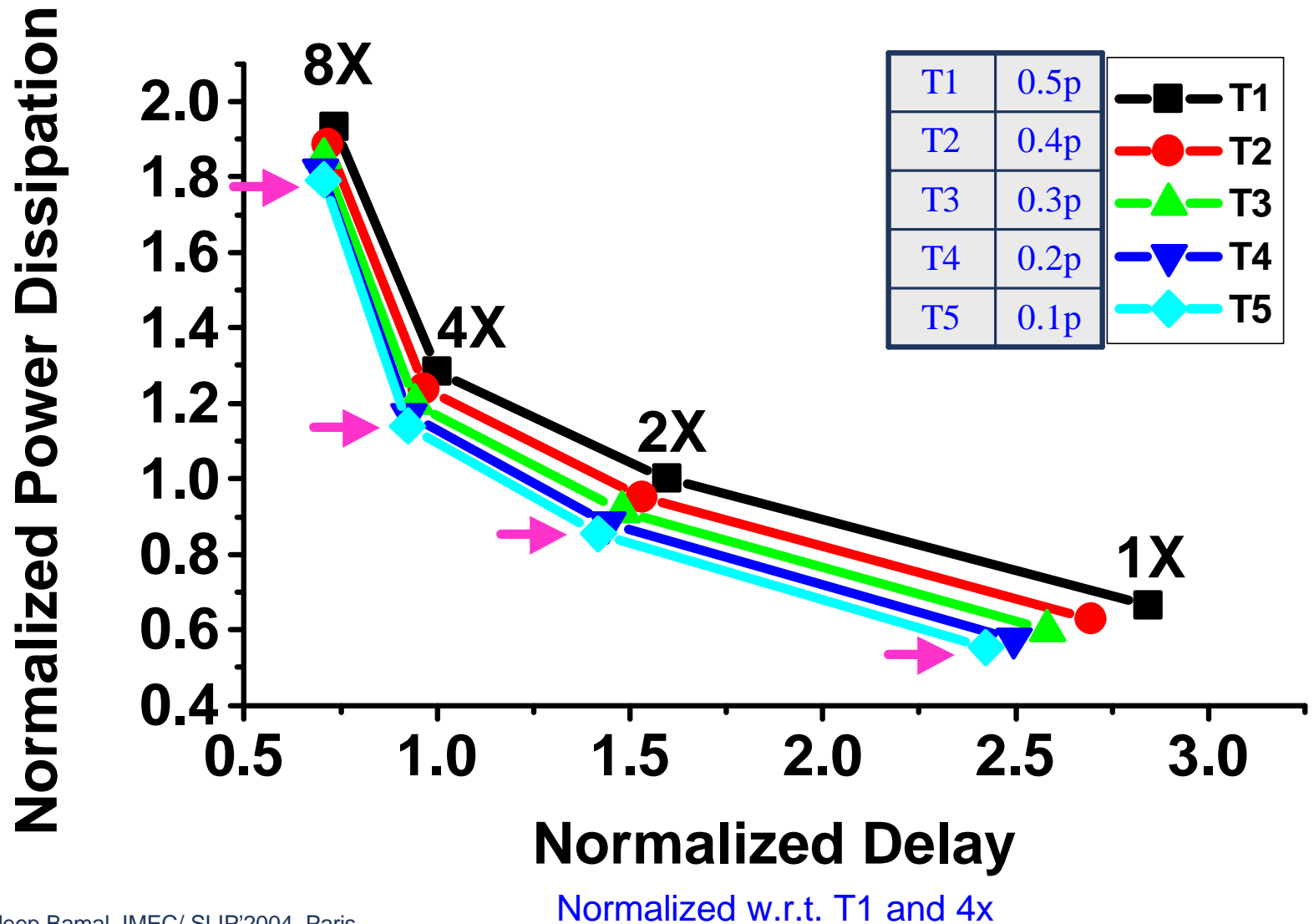


Including Buffer Sizing

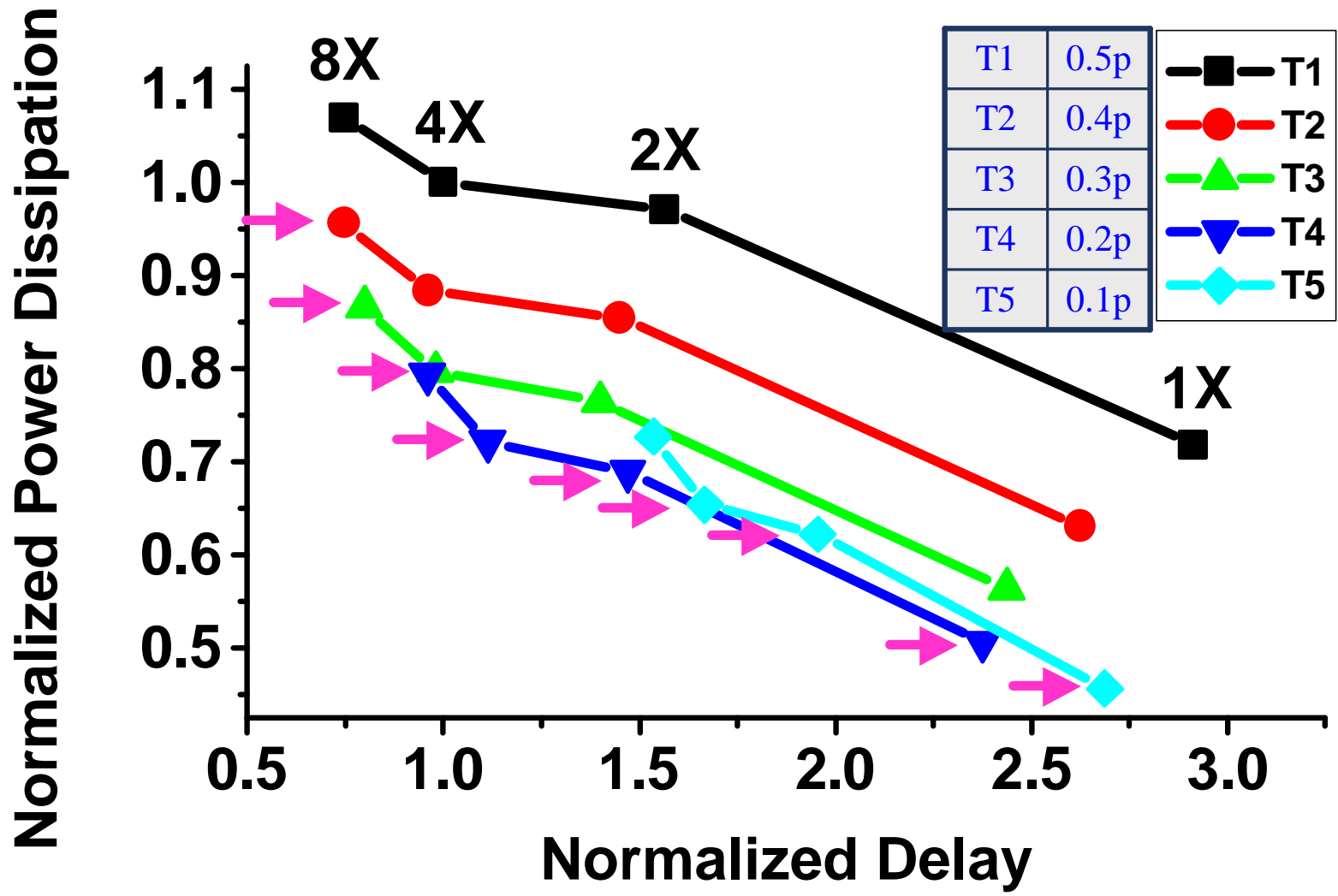




Local Interconnects (length = 40 um)



Global Interconnects (length = 800 μm)



Normalized w.r.t. T1 and 4x

- Exploration can be done for interconnect dimensions
 - Informed choice for interconnect dimensions
- Local Interconnects (very short wires...)
 - Not much Trade off is possible by width-only exploration
 - Smallest width is the best solution for constant pitch in context of power and delay optimization
- Intermediate Interconnects
 - Significant Trade off can be made between delay and power
- Global Wires
 - Dissipation can be traded for reducing the delay
 - Simultaneous buffer sizing and wire sizing is the best option
- Future work
 - Variable pitch and height exploration
 - Better Signal Integrity evaluation models
 - Effect on area

Thank you!



questions